

Silicon NPN Power Transistors

2SD896

**DESCRIPTION**

- With TO-3PN package
- Complement to type 2SB776
- Wide area of safe operation

**APPLICATIONS**

- 100V/7A, AF 40W output applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

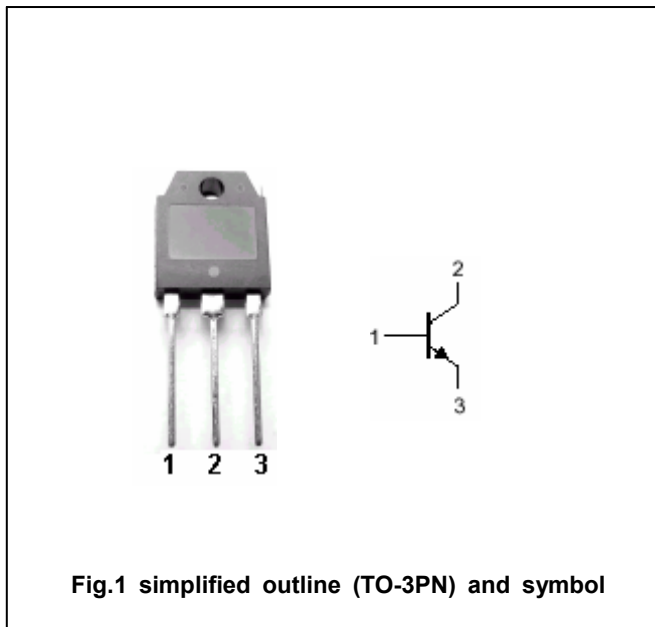


Fig.1 simplified outline (TO-3PN) and symbol

**Absolute maximum ratings(Tc=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	120	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	100	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	6	V
I <sub>C</sub>	Collector current (DC)		7	A
I <sub>CM</sub>	Collector current-peak		11	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	70	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-40~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =50mA ; R <sub>BE</sub> =∞	100			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =5mA ; I <sub>E</sub> =0	120			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =5mA ; I <sub>C</sub> =0	6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A ; I <sub>B</sub> =0.4A		0.6	2.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =80V I <sub>E</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =4V ; I <sub>C</sub> =0			0.1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	60		200	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =4A ; V <sub>CE</sub> =5V	20			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V		15		MHz
C <sub>OB</sub>	Collector output capacitance	f=1MHz ; V <sub>CB</sub> =10V		140		pF

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =1.0A ; I <sub>B1</sub> =-I <sub>B2</sub> =0.1A R <sub>L</sub> =20Ω ; V <sub>CC</sub> =20V		0.2		μs
t <sub>stg</sub>	Storage time			6.0		μs
t <sub>f</sub>	Fall time			0.6		μs

◆ h<sub>FE-1</sub> Classifications

D	E
60-120	100-200

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PACKAGE OUTLINE

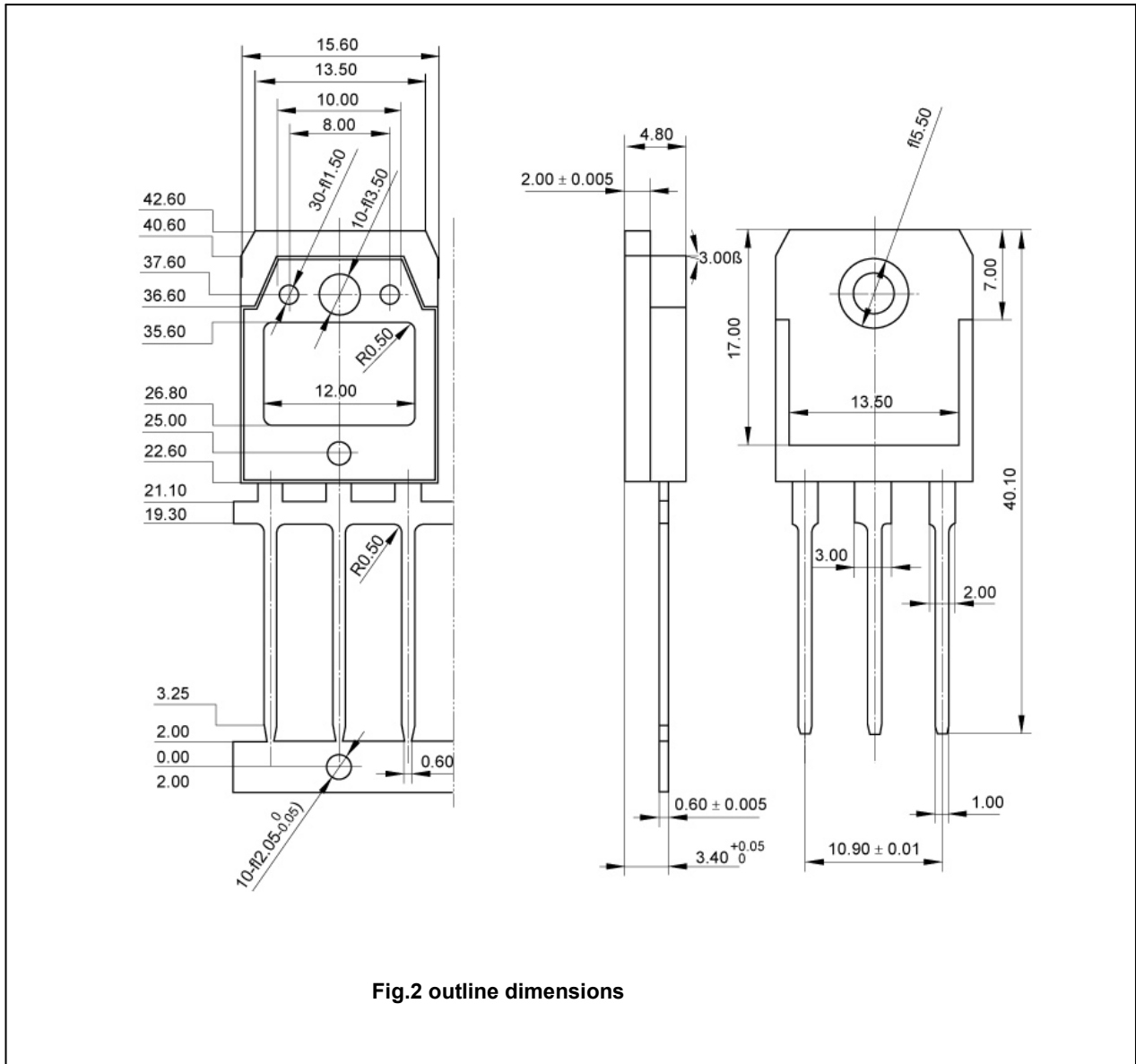


Fig.2 outline dimensions

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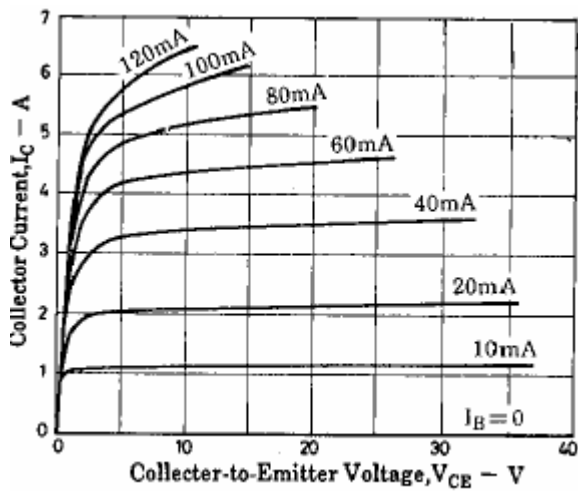


Fig.3 Static Characteristic

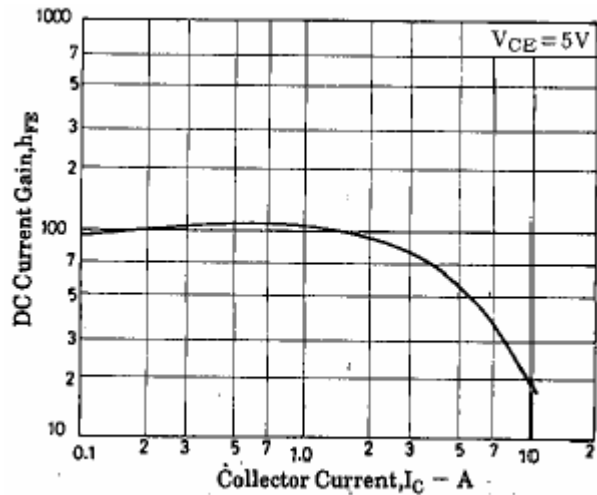


Fig.4 DC current Gain

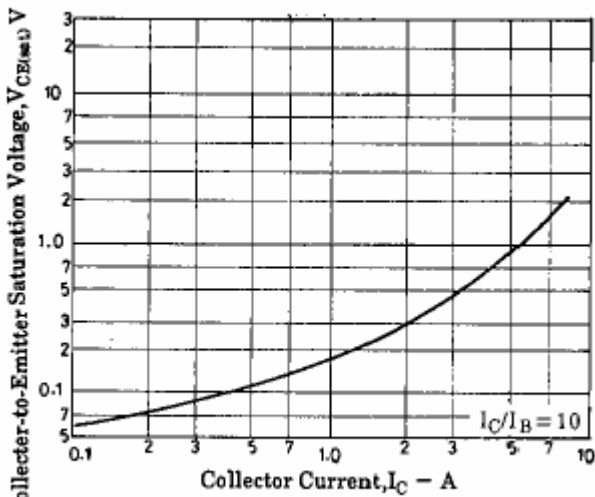


Fig.5 Collector-Emmitter Saturation Voltage

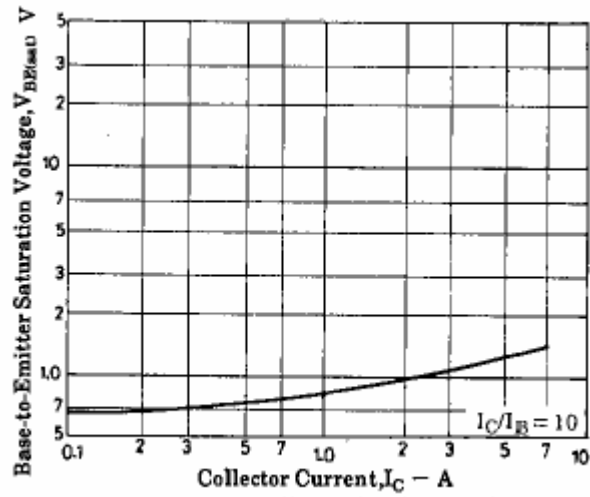


Fig.6 Base-Emmitter Saturation Voltage

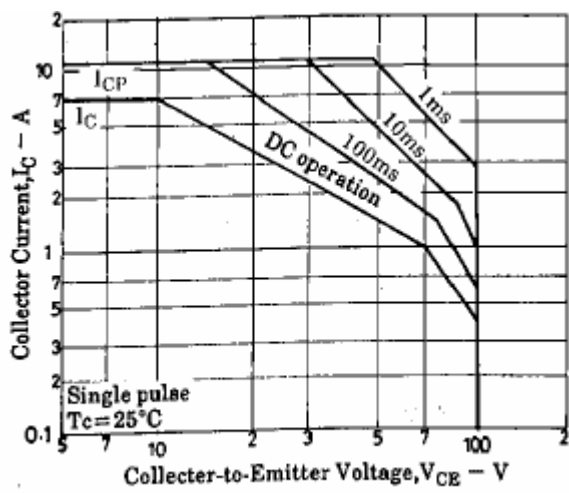


Fig.7 Safe Operating Area